



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



HSMP-386J

High Power RF PIN Diode



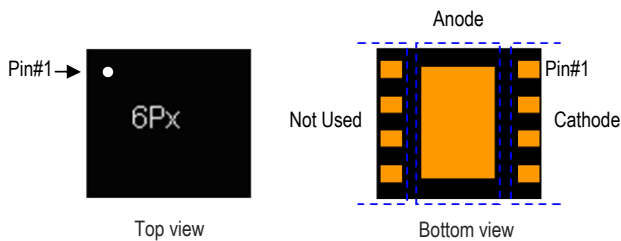
Data Sheet

Description

Avago Technologies' HSMP-386J is a High Power RF PIN Diode specifically design for high power handling and low distortion Transmit/Receive switching application. It is housed in QFN 2x2mm size package which is having good thermal resistance.

The unique with 8 dies in parallel configuration results to low IL performance and low series resistance. The HSMP-386J Power diode is built with match diode to ensure consistency in performance.

Package Marking & Orientation



Notes:
 6P = Device Code
 x = Month code indicates the month of manufacture

Features

- High Power Surface Mount Package QFN 2x2
- Match Diode for Consistent Performance
- Low Bias Current Requirement
- Low Series Resistance
- Low Insertion Loss & High Isolation
- Better Thermal Conductivity for Higher Power Dissipation
- Low Failure in Time (FIT) Rate
- Lead-free Option Available
- MSL1 & Lead Free
- Tape & Reel Option Available

Specifications

- Low RS Switching typically 0.65Ω @ 100MHz, 50mA
- High Power Handling Up to 10W (40dBm) at 2GHz, 50mA

Application

- High Power Transmit / Receive Switch for Cellular Infrastructure and Two Way Radio

Circuit Diagram of HSMP-386J

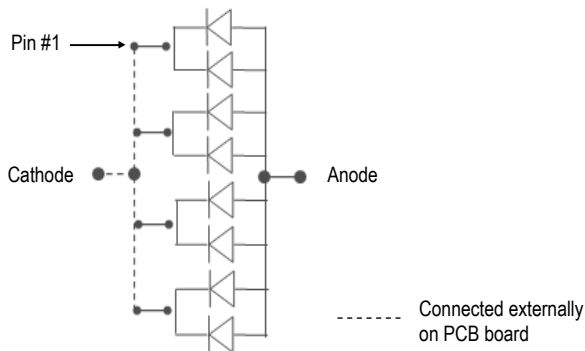


Table 1. Absolute Maximum Ratings ^[1] at T_C = +25°C

Symbol	Parameter	Unit	Max Rating
I _F	Forward Current (1μs Pulse) per die ^[2]	Amp	1
P _{IV}	Peak Inverse Voltage	V	100
T _j	Junction Temperature	°C	150
T _{stg}	Storage Temperature	°C	-60 to 150
θ _{jc}	Thermal Resistance ^[3]	°C/W	45
DC P _{diss}	DC Power Dissipation ^[4]	W	2.0

Notes:

1. Operation in excess of any one of these conditions may result in permanent damage to the device.
2. Eight dice are connected in parallel for this device.
3. T_C = +25°C, where T_C is defined to be the temperature at the package pins where contact is made to the circuit board.
4. Maximum DC P_{diss} measured without RF input and maximum rating is base on device junction temperature.

$$P_{diss} = \frac{T(\text{Max.Operating}) - 25^{\circ}\text{C}}{\text{Thermal Resistance}}$$

Table 2. Electrical Performance at T_C = +25°C

	Minimum Breakdown Voltage V _{BR} (V)	Typical Forward Voltage V _f (V)	Maximum Series Resistance R _S (Ohm)	Maximum Total Capacitance C _T (pF)
	100	0.85	0.77	1.25
Test Conditions	V _R = V _{BR} Measure I _R ≤ 5uA	I _F = 50mA	I _F = 50 mA f = 100 MHz	V _R = 50V f = 1MHz

Table 3. Typical Performance at T_C = +25°C

	Series Resistance R _S (Ω)	Carrier Lifetime (nS)	Reverse Recovery Time T _{rr} (nS)	Total Capacitance C _T (pF)
	0.65	260	130	0.75
Test Conditions	I _F = 50mA f = 100MHz	I _F = 50mA I _R = 100mA	V _R = 5V I _F = 50mA 90% Recovery	V _R = 50V f = 1MHz

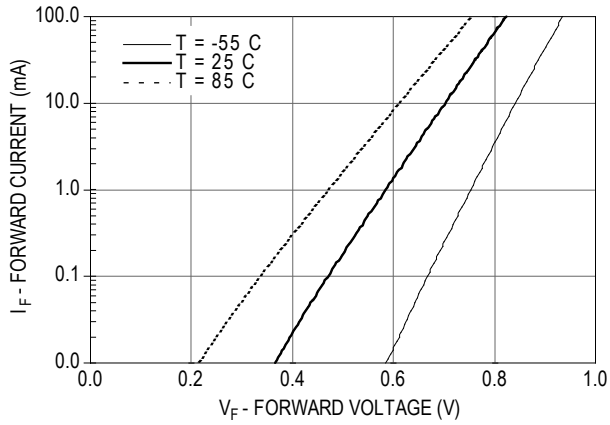


Figure 1. Forward Current vs. Forward Voltage

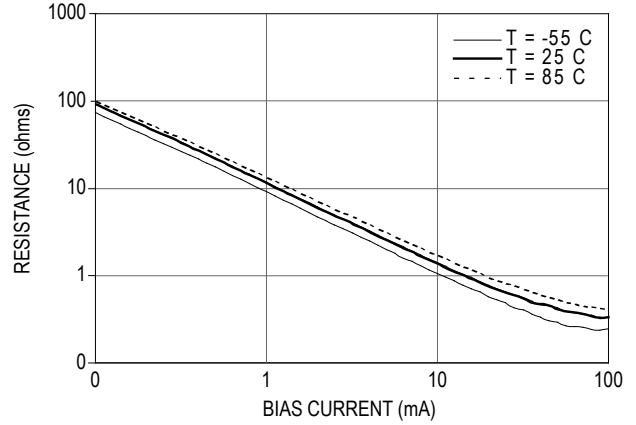


Figure 2. Typical RF Resistance vs. Forward Bias Current.

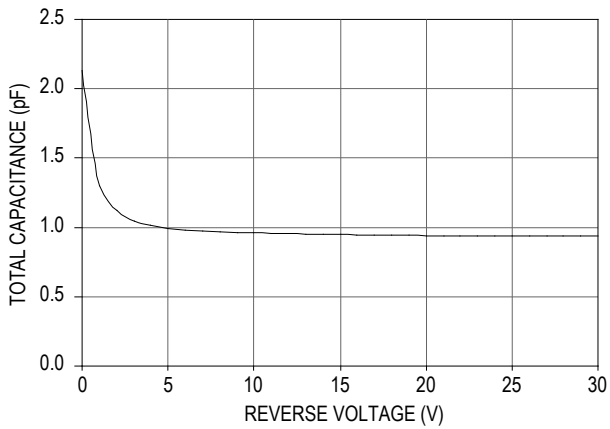


Figure 3. RF Capacitance vs. Reverse Bias Voltage

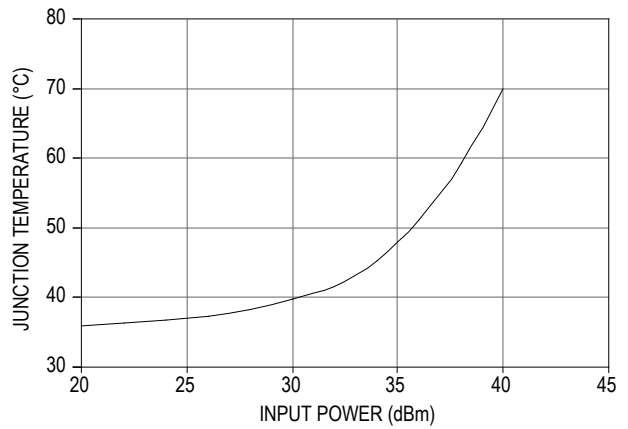
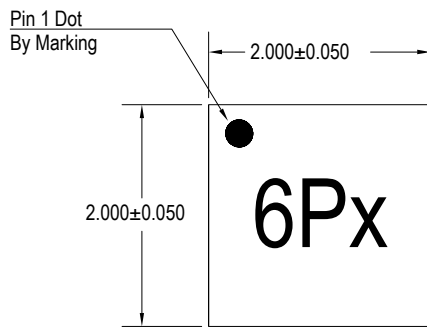


Figure 4. Input Power vs. Junction Temperature [1]

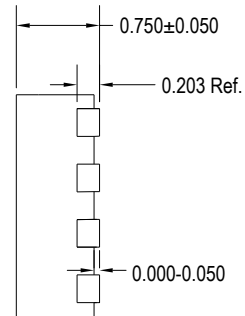
Notes:

1. Test conditions: $f = 2.1\text{GHz}$, $I_F = 50\text{mA}$
2. Typical values were derived using limited samples during initial product characterization and may not be representative of the overall distribution.

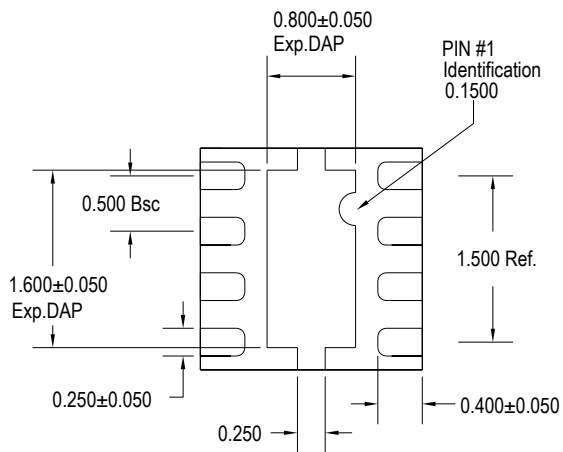
QFN 2x2 Package Dimension



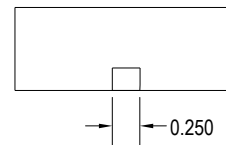
Top View



Side View



Bottom View

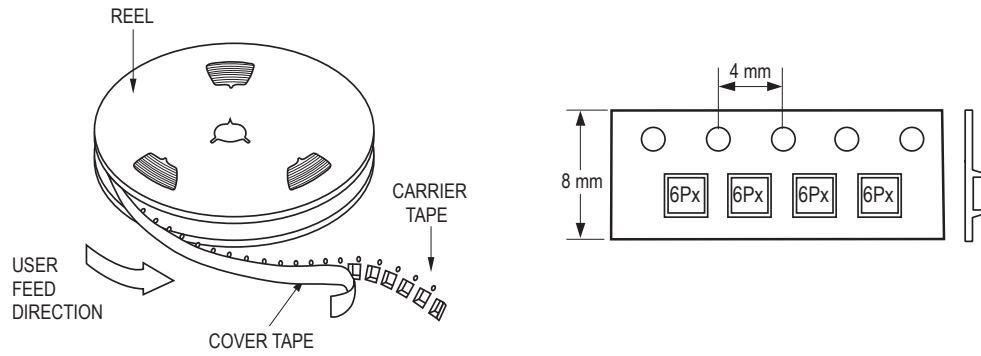


Top View

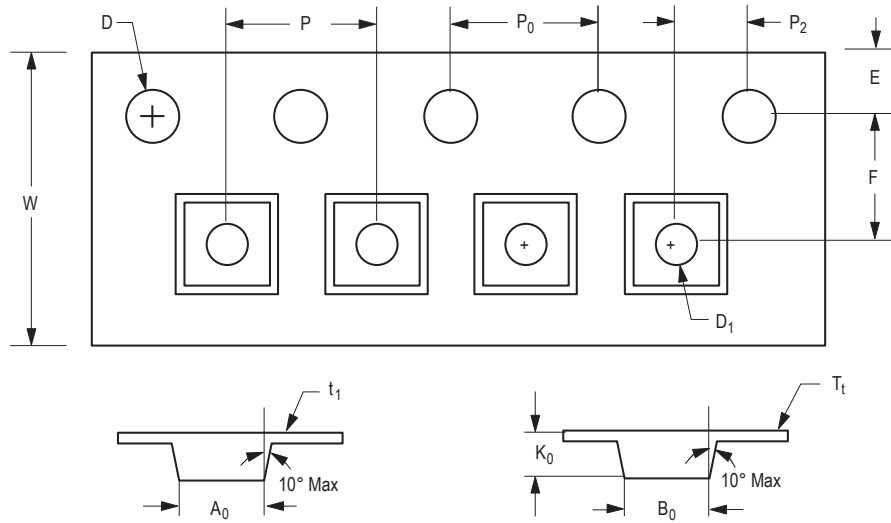
Note:

1. All dimensions in millimeters.
2. Dimensions are inclusive of plating.
3. Dimensions are exclusive of mold flash and metal burr.

Device Orientation



Tape Dimensions



DESCRIPTION		SYMBOL	SIZE (mm)	SIZE (inches)
CAVITY	LENGTH	A_0	2.30 ± 0.05	0.091 ± 0.004
	WIDTH	B_0	2.30 ± 0.05	0.091 ± 0.004
	DEPTH	K_0	1.00 ± 0.05	0.039 ± 0.002
	PITCH	P	4.00 ± 0.10	0.157 ± 0.004
	BOTTOM HOLE DIAMETER	D_1	$1.00 + 0.25$	$0.039 + 0.002$
PERFORATION	DIAMETER	D	1.50 ± 0.10	0.060 ± 0.004
	PITCH	P_0	4.00 ± 0.10	0.157 ± 0.004
	POSITION	E	1.75 ± 0.10	0.069 ± 0.004
CARRIER TAPE	WIDTH	W	$8.00 + 0.30$	0.315 ± 0.012
	THICKNESS	t_1	8.00 ± 0.10 0.254 ± 0.02	0.315 ± 0.004 0.010 ± 0.0008
COVER TAPE	WIDTH	C	5.4 ± 0.10	0.205 ± 0.004
	TAPE THICKNESS	T_1	0.062 ± 0.001	0.0025 ± 0.0004
DISTANCE	CAVITY TO PERFORATION (WIDTH DIRECTION)	F	3.50 ± 0.05	0.138 ± 0.002
	CAVITY TO PERFORATION (LENGTH DIRECTION)	P_2	2.00 ± 0.05	0.079 ± 0.002

For product information and a complete list of distributors, please go to our web site: www.avagotech.com

Avago, Avago Technologies, and the A logo are trademarks of Avago Technologies, Limited in the United States and other countries. Data subject to change. Copyright © 2007 Avago Technologies Limited. All rights reserved.
AV02-0819EN - December 25, 2007

AVAGO
TECHNOLOGIES